

DATE: July 6, 2026

PCN #: 2800

PCN Title: Fab Porting from SK keyfoundry Fab3 to SK keyfoundry Fab4, Cheongju, South Korea, and Product Marking Change

Dear Customer:

This is an announcement of change(s) to products that are currently being offered by Diodes Incorporated.

We request that you acknowledge receipt of this notification within 30 days of the date of notification by contacting your local Diodes sales representative. If you require samples for evaluation purposes, please submit a corresponding request within 30 days as well. Otherwise, samples may not be built prior to the implementation of the announced change(s).

The change(s) announced in this PCN will not be implemented prior to the target implementation date, i.e. 90 days from the stated notification date, unless Diodes receives written customer approval before that date.

Previously agreed upon customer specific product and/or process change requirements will be addressed separately.

For questions or clarification regarding this PCN, please contact your local Diodes sales representative.

Sincerely,

Diodes Incorporated PCN Team



PRODUCT CHANGE NOTICE

PCN-2800-REV1

Notification Date:	Implementation Date:	Product Family:	Change Type:	PCN #:
July 6, 2026	October 5, 2026	Analog	Additional Wafer Source (SKKF Fab4), Top Marking Change	2800
TITLE				
Fab Porting from SK keyfoundry (SKKF) Fab3 to SK keyfoundry (SKKF) Fab4, Cheongju, South Korea, and product top marking change.				
DESCRIPTION OF CHANGE				
SK keyfoundry Fab3 has discontinued their 0.5µm wafer process technologies. To ensure continuity of supply, Diodes Incorporated has qualified additional wafer source SK keyfoundry (SKKF) Fab4 located in Cheongju, South Korea. This PCN is being issued to notify customers of the aforementioned change. For some products currently produced in SKKF Fab3, a die shrink has been made from 0.5 µm CMOS to 0.35 µm CMOS at SKKF Fab4. Top markings will be updated for all products as outlined below. • External wafer source SKKF (Fab4) located in Cheongju, South Korea • Diodes internal A/T site (CAT) in Chengdu, China • External AT site JCET Group Co., Ltd. (JCET) located in Suqian, China Full electrical characterization and high reliability testing has been completed on representative part numbers to ensure there is no change to device functionality or electrical specifications in the datasheet. There will be no change to Fit or Function of products affected.				
IMPACT				
Continuity of Supply. No change in datasheet electrical parameters and product performance.				
PRODUCTS AFFECTED				
• Table 1 – Fab porting from SKKF Fab3 to SKKF Fab4, and top marking change. • Table 2 – Fab porting from SKKF Fab3 to SKKF Fab4, wafer process change from 0.5µm CMOS to 0.35µm CMOS, and top marking change • Table 3 – Top marking change • Table 4 – Top marking change for AT Sites JCET and CAT				
WEB LINKS				
Manufacturer's Notice:	https://www.diodes.com/quality/product-change-notices/diodes-product-change-notices/			
For More Information Contact:	https://www.diodes.com/about/contact-us/contact-sales/			
Data Sheet:	https://www.diodes.com/catalog/			

DISCLAIMER

Unless a Diodes Incorporated Sales representative is contacted in writing within 30 days from the notification date of this PCN, all changes described in this announcement are considered approved.

Table 1 – Fab porting from SKKF Fab3 to SKKF Fab4, and top marking change, see table 1A

PI5C3257LEX	PI5C3257QEX	PI5V330AQEX	PI5V330QEX		
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Table 2 – Fab porting from SKKF Fab3 to SKKF Fab4, wafer process change from 0.5µm CMOS to 0.35µm CMOS, and top marking change, see table 2A

PI3CH3244LEX	PI3CH3244ZHEX	PI3CH3345LEX	PI3CH3345ZHEX	PI3CH800LEX	PI3CH800QEX
PI3CH800ZHEX					

TABLE 3 – Top marking change, see table 3A

PI3C3125LEX	PI3C3125QEX	PI3C3126LEX	PI3C3126QEX	PI3C3305LEX	PI3C3306LEX
PI3C3306UEX	PI3CH281QEX	PI3CH480LEX	PI3CH480QEX	PI3USB102GZLEX	PI3V312LEX
PI3V312QEX	PI3VT3306LE	PI3VT3306LEX	PI4MSD5V9540BUEX	PI4MSD5V9542ALEX	PI4MSD5V9543ALEX
PI4MSD5V9544ALEX	PI4MSD5V9545ALEX	PI4MSD5V9546ALEX	PI4MSD5V9546AZYEX	PI4ULS5V201TAEX	PI4ULS5V201XVEX
PI4ULS5V202Q1UEX	PI4ULS5V202UEX	PI4ULS5V202XVEX	PI5A124TEX	PI5A3166CEX	PI5A3166TAEX
PI5A3167CCEX	PI5A3167CTAEX	PI5A4157CEX	PI5A4157TAEX	PI5C3125QEX	PI5C3126QEX
PI5C3253LEX	PI5C3253QEX	PI5C3303TEX	PI5C3305LEX	PI5C3306LEX	PI5V331QEX
PI6ULS5V9509UEX	PI6ULS5V9515AUEX	PI6ULS5V9617AUEX			

Table 4 – Top marking change for AT Sites JCET and CAT, see table 4A

PI5A3157CEX	PI5A4599BCEX				
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Table 1A – Top Marking Change

Sample Part: PI5C3257LEX Package: TSSOP-16

Current Marking

L Package



YY: Year
WW: Workweek
1st X: Assembly Site Code
2nd X: Fab Site Code
Bar above "I" means Fab3 of MGN
Bar above fab code means Cu wire

New Marking

L Package



YY: Year
WW: Workweek
1st X: Assembly Site Code
2nd X: Fab Site Code
Overbar Symbol: Internal Code

Table 2A – Top Marking Change

Sample Part: PI3CH3244ZHEX Package: W-QFN3545-20

Current Marking



Z: Fixed Code
YW: Date Code (Year & Work Week)
G: Assembly Site Code (1st G)
G: Wafer Fab Site Code
Bar above "I" means Fab3 of MGN
Bar above 2nd "G" means Cu wire

New Marking



Z: Fixed Code
YW: Date Code (Year & Work Week)
G: Assembly Site Code (1st G)
G: Wafer Fab Site Code
Overbar Symbol: Internal Code

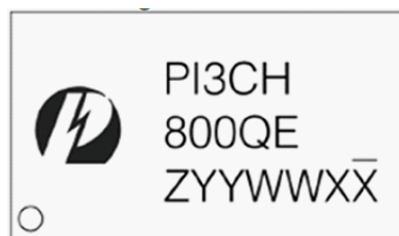
Sample Part: PI3CH800QEX Package: QSOP-20

Current Marking



Z: Fixed Code
YY: Year
WW: Workweek
1st X: Assembly Site Code
2nd X: Fab Site Code

New Marking



Z: Fixed Code
YY: Year
WW: Workweek
1st X: Assembly Site Code
2nd X: Fab Site Code

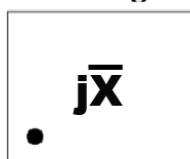
Overbar Symbol: Internal Code

Table 3A – Top Marking Change

Sample Part: PI4ULS5V202XVEX Package:U-DFN1616-8

Current Marking

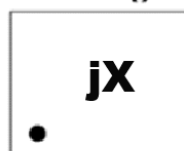
XV Package



j: PI4ULS5V202XVE
X: Date Code (Year & Workweek)
Bar above "X" means Fab3 of MGN

New Marking

XV Package



j: PI4ULS5V202XVE
X: Date Code (Year & Workweek)
Overbar Symbol: Internal Code

Sample Part: PI4ULS5V202Q1UEX

Package: MSOP-8

Current Marking



Y: Date Code (Year)
W: Date Code (Workweek)
1st X: Assembly Site Code
2nd X: Fab Site Code
Bar above "L" mean Fab3 of MGN

New Marking



Y: Date Code (Year)
W: Date Code (Workweek)
1st X: Assembly Site Code
2nd X: Fab Site Code
Overbar Symbol: Internal Code

Table 4A – Top Marking Change

Sample Part: PI5A4599CEX

Package: SOT363

Current Marking



Y: Date Code (Year)
W: Date Code (Workweek)
Bar above last "W" indicates Cu wire

New Marking



XX: Date Code (Year & Workweek)
Bar above "Z" indicates RoHS compliance
Bar above last "X" indicates Cu wire
Bar under last "X" for external site (e.g., JCET)
No bar under the last "X" for internal site (e.g., CAT)

Description: SKKF EOL HL50S and HL50L process in Fab 3 and asked DIODES to transfer MP to Fab 4, Fab3 and Fab4 shared masks

Submitted By: _____
Approved By: Darius Crenshaw 01/15/2026



Certificate of Design, Construction & Qualification

Description:PI3CH3244/ 3245/ 3345A KeyFundray FAB4 BES01-AC Standard Qual Plan Template

				Qual Device 1		Qual Device 2		Qual Device 3		Qual Device 4		Qual Device 5		Qual Device 6		QBS Device 1		QBS Device 2		QBS Device 3		QBS Device 4		QBS Device 5				
Part Number				PI3CH3244AL20-13		PI3CH3345AZH20-7		PI3CH3245JS20-13		PI3CH3245L20-13 PI3CH3345AL20-13		PI3CH3244AZH20-7 PI3CH3345AZH20-7		PI3CH3244AJ520-13 PI3CH3345AJ520-13		LX50108QLEX		PI3B3245ZHEX		PI3CH3253LEX		PI3CH3257LEX		PI3CH3253QEX				
PG #				1.0		1.0		1.0		1.0		1.0		1.0		PG1.0/1.2		PG1.0		A		A		A				
Package				TSSOP20		W-QFN3545-20		QSSOP20		TSSOP20		W-QFN3545-20		QSSOP20		TSSOP20		W-QFN3545-20		TSSOP16 (L16)		TSSOP16 (L16)		QSSOP16 (Q16)				
Wire Bond, Cu Piller, CSP				Wire Bond		Wire Bond		Wire Bond		Wire Bond		Wire Bond		Wire Bond		Wire Bond		Wire Bond		Wire Bond		Wire Bond		Wire Bond				
MSL Level				MSL-1		MSL-1		MSL-1		MSL-1		MSL-1		MSL-1		MSL-1		MSL-1		MSL-1		MSL-1		MSL-1				
Die Quantity (eg. Die per package)				1		1		1		1		1		1		1		1		1		1		1				
Die Name(s)				BS01-AC		BS01-AC		BS01-AC		BS01-AC		BS01-AC		BS01-AC		LS08-CA		BS25-D143		BS01-AB		BS01-AB		BS01-AB				
Die Size (W/L/Thickness)				0.74 x 1.50 mm		0.74 x 1.50 mm		0.74 x 1.50 mm		0.74 x 1.50 mm		0.74 x 1.50 mm		0.74 x 1.50 mm		1.160*1.800mm		0.82*1.16mm		0.74 x 1.50 mm		0.74 x 1.50 mm		0.74 x 1.50 mm				
Die Process / Technology				Key-Foundry 0.35um HL355, 2P4M, 5V NMOS/PMOS ONLY (no 3.3V device), Low-Vt 5V PMOS, Hi R 1KOhm Poly Resistor, and Thick Top Metal (4um thickness), Salicided process, Deep N well		Key-Foundry 0.35um HL355, 2P4M, 5V NMOS/PMOS ONLY (no 3.3V device), Low-Vt 5V PMOS, Hi R 1KOhm Poly Resistor, and Thick Top Metal (4um thickness), Salicided process, Deep N well		Key-Foundry 0.35um HL355, 2P4M, 5V NMOS/PMOS ONLY (no 3.3V device), Low-Vt 5V PMOS, Hi R 1KOhm Poly Resistor, and Thick Top Metal (4um thickness), Salicided process, Deep N well		Key-Foundry 0.35um HL355, 2P4M, 5V NMOS/PMOS ONLY (no 3.3V device), Low-Vt 5V PMOS, Hi R 1KOhm Poly Resistor, and Thick Top Metal (4um thickness), Salicided process, Deep N well		Key-Foundry 0.35um HL355, 2P4M, 5V NMOS/PMOS ONLY (no 3.3V device), Low-Vt 5V PMOS, Hi R 1KOhm Poly Resistor, and Thick Top Metal (4um thickness), Salicided process, Deep N well		Key-Foundry 0.35um HL355, 2P4M, 5V NMOS/PMOS ONLY (no 3.3V device), Low-Vt 5V PMOS, Hi R 1KOhm Poly Resistor, and Thick Top Metal (4um thickness), Salicided process, Deep N well		Key-Foundry 0.35um HL355, 2P4M		0.35UM CMOS(1P3M)		Key-Foundry 0.35um HL355, 2P4M, 5V NMOS/PMOS ONLY (no 3.3V device), Low-Vt 5V PMOS, Hi R 1KOhm Poly Resistor, and Thick Top Metal (4um thickness), Salicided process, Deep N well		Key-Foundry 0.35um HL355, 2P4M, 5V NMOS/PMOS ONLY (no 3.3V device), Low-Vt 5V PMOS, Hi R 1KOhm Poly Resistor, and Thick Top Metal (4um thickness), Salicided process, Deep N well		Key-Foundry 0.35um HL355, 2P4M, 5V NMOS/PMOS ONLY (no 3.3V device), Low-Vt 5V PMOS, Hi R 1KOhm Poly Resistor, and Thick Top Metal (4um thickness), Salicided process, Deep N well				
Wire Bond Material (Au, Cu, Al)				PdCu		PdCu		PdCu		PdCu		PdCu		PdCu		PdCu		PdCu		PdCu		PdCu		PdCu				
Wire Diameter				0.8mil		0.8mil		0.8mil		0.8mil		0.8mil		0.8mil		0.8mil		0.8mil		0.8mil		0.8mil		0.8mil				
Wafer FAB				Key-Foundry		Key-Foundry		Key-Foundry		Key-Foundry		Key-Foundry		Key-Foundry		Key-Foundry		Key-Foundry		Key-Foundry		Key-Foundry		Key-Foundry				
Wafer Diameter				8 inches (200 mm)		8 inches (200 mm)		8 inches (200 mm)		8 inches (200 mm)		8 inches (200 mm)		8 inches (200 mm)		8 inches (200 mm)		8 inches (200 mm)		8 inches (200 mm)		8 inches (200 mm)		200mm				
Wafer Thickness				725um		725um		725um		725um		725um		725um		725um		725um		725um		725um		725um				
Top Metal Type/Bond Pad Composition				1/TiN/Al-Cu0.5%/TiN		1/TiN/Al-Cu0.5%/TiN		1/TiN/Al-Cu0.5%/TiN		1/TiN/Al-Cu0.5%/TiN		1/TiN/Al-Cu0.5%/TiN		1/TiN/Al-Cu0.5%/TiN		AlCu		1/TiN/Al-Cu0.5%/TiN		1/TiN/Al-Cu0.5%/TiN		1/TiN/Al-Cu0.5%/TiN		1/TiN/Al-Cu0.5%/TiN				
Top Metal Thickness				4 um		4 um		4 um		4 um		4 um		4 um		4 um		4 um		4 um		4 um		4 um				
Die passivation thickness range				1.725 +/- 0.1725 um		1.725 +/- 0.1725 um		1.725 +/- 0.1725 um		1.725 +/- 0.1725 um		1.725 +/- 0.1725 um		1.725 +/- 0.1725 um		N/A		N/A		1.725 +/- 0.1725 um		1.725 +/- 0.1725 um		1.725 +/- 0.1725 um				
Glass Transition Temp				150 degrees C		150 degrees C		150 degrees C		150 degrees C		150 degrees C		150 degrees C		150 degrees C		150 degrees C		150 degrees C		150 degrees C		150 degrees C				
Max Junction Temp				122.69 degree C		124.005 degree C		141.5 degree C		122.69 degree C		124.005 degree C		141.5 degree C		124.005 degree C		125 degree C		125 degree C		125 degree C		125 degree C				
Max Thermal resistance Junc (ambient)				75-38 C/W		78.01 C/W		113 C/W		75-38 C/W		78.01 C/W		113 C/W		75-38 C/W		N/A		N/A		N/A		N/A				
Metal Layers				4		4		4		4		4		4		4		3		4		4		4				
Metal Density per Layer				M1: 64.5% M2: 44.2% M3 44.5% MAT 59.1%		M1: 64.5% M2: 44.2% M3 44.5% MAT 59.1%		M1: 64.5% M2: 44.2% M3 44.5% MAT 59.1%		M1: 64.5% M2: 44.2% M3 44.5% MAT 59.1%		M1: 64.5% M2: 44.2% M3 44.5% MAT 59.1%		M1: 64.5% M2: 44.2% M3 44.5% MAT 59.1%		N/A		N/A		M1: 64.5% M2: 44.2% M3 44.5% MAT 59.1%		M1: 64.5% M2: 44.2% M3 44.5% MAT 59.1%		M1: 64.5% M2: 44.2% M3 44.5% MAT 59.1%				
Min Metal Width				0.5um		0.5um		0.5um		0.5um		0.5um		0.5um		N/A		N/A		0.5um		0.5um		0.5um				
Min Metal Spacing				0.45um		0.45um		0.45um		0.45um		0.45um		0.45um		N/A		N/A		0.45um		0.45um		0.45um				
Power Consumption				0.25W		0.25W		0.25W		0.25W		0.25W		0.25W		N/A		N/A		0.25W		0.25W		0.25W				
Number of Transistors				613		613		613		613		613		613		N/A		N/A		613		613		613				
Background/Thickness				10mil		7mil		15mil		10mil		7mil		15mil		N/A		140±10um		10mil		10mil		≤15mil				
Background Location				GTK		GTK		GTK		GTK		GTK		GTK		GTK		GTK		GTK		GTK		GTK				
Bond Type (at Die)				Ball		Ball		Ball		Ball		Ball		Ball		Ball		Ball		Ball		Ball		Ball				
Bond Type (at LF)				Wedge		Wedge		Wedge		Wedge		Wedge		Wedge		Wedge		Wedge		Wedge		Wedge		Wedge				
DB Epoxy/Solder Type				EPOXY		EPOXY		EPOXY		EPOXY		EPOXY		EPOXY		EPOXY		EPOXY		EPOXY		EPOXY		EPOXY				
Die Attach Material				EN-4900GC		CRM-1076DJ-G		CRM-1076DJ-G		EN-4900GC		CRM-1076DJ-G		CRM-1076DJ-G		EN-4900GC		CRM-1076DJ-G		EME 1076DJ-G		EME 1076DJ-G		EME 1076DJ-G				
Min Bond Pad Pitch				110um		110um		110um		110um		110um		110um		110um		110um		110um		110um		110um				
# of pad/ball/pin Pitch				16/0.65mm		16/0.65mm		16/0.65mm		16/0.65mm		16/0.65mm		16/0.65mm		16/0.65mm		114.8 um		16/0.65mm		16/0.65mm		16/0.65mm				
Leadframe Type (Stamped or Etched)				Stamped		Stamped		Stamped		Stamped		Stamped		Stamped		Stamped		Etched		Stamped		Stamped		Stamped				
Ag plated or Bare Cu				Bare Cu		Bare Cu		Bare Cu		Bare Cu		Bare Cu		Bare Cu		Bare Cu		Bare Cu		Bare Cu		Bare Cu		Bare Cu				
Lead Frame Manufacturer				FUSHENG		SHINKO		FUSHENG		FUSHENG		FUSHENG		SHINKO		FUSHENG		Fusheng		Fusheng		Fusheng		FUSHENG				
Molding Compound Type				G700H		G700H		G700L		G700H		G700H		G700H		G700H		G700H		EME G700LY		EME G700LY		EME G700LY				
Molding Compound Manufacturer				Sumitomo		Sumitomo		Sumitomo		Sumitomo		Sumitomo		Sumitomo		Sumitomo		Sumitomo		Sumitomo		Sumitomo		Sumitomo				
Green Compound (Yes/No)				Yes		Yes		Yes		Yes		Yes		Yes		Yes		Yes		Yes		Yes		Yes				
Lead-Free (Yes/No)				Yes		Yes		Yes		Yes		Yes		Yes		Yes		Yes		Yes		Yes		Yes				
Assembly Site/ Location				GTK		GTK		GTK		GTK		GTK		GTK		GTK		GTK		GTK		GTK		GTK				
Test Site/ Location				GTK		GTK		GTK		GTK		GTK		GTK		GTK		GTK		GTK		GTK		GTK				
Readability Test Site				GTK/IST/BCD		GTK/IST/BCD		GTK/IST/BCD		GTK/IST/BCD		GTK/IST/BCD		GTK/IST/BCD		GTK/IST/BCD		BCD		BCD		GTK/IST-TW		GTK/IST-TW				
Readability Testing																												
Test				Test Conditions	Duration / Limits	Fail/SS	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail		
Test Group A - Accelerated Environment Stress Tests																												
MSL1 Pre-cond	(JESD22-A113) Bake 125C			24 Hrs	0/154		QBS to QBS Device 1		QBS to QBS Device 2		X	PASS	QBS to QBS Device 1		QBS to QBS Device 2		QBS to Qual Device 3/ QBS Device 5		3X	PASS	3X	PASS	X	PASS	QBS to QBS Device 3		X	PASS
	Soak 85C, 85% RH			168Hrs	0/154		QBS to QBS Device 1		QBS to QBS Device 2		X	PASS	QBS to QBS Device 1		QBS to QBS Device 2		QBS to Qual Device 3/ QBS Device 5		3X	PASS	3X	PASS	X	PASS	QBS to QBS Device 3		X	PASS
	(JESD22-A104) -65C-150C Mounted on PCB Board (Daughter Card)			500 cycles	0/77		QBS to QBS Device 1		QBS to QBS Device 2		X	PASS	QBS to QBS Device 1		QBS to QBS Device 2		QBS to Qual Device 3/ QBS Device 5		3X	PASS	3X	PASS	X	PASS	QBS to QBS Device 3		X	PASS
Temp Cycle (TC)				1000 cycles	0/77		QBS to QBS Device 1		QBS to QBS Device 2		X	PASS	QBS to QBS Device 1		QBS to QBS Device 2		QBS to Qual Device 3/ QBS Device 5		3X	PASS	3X	PASS	X	PASS	QBS to QBS Device 3		X	PASS
	JESD22-A101/A110 130C, 85%RH 33.3 psia Vcc = Op Max			96 Hrs	0/77		QBS to QBS Device 1		QBS to QBS Device 2		X	PASS	QBS to QBS Device 1		QBS to QBS Device 2		QBS to Qual Device 3/ QBS Device 5		3X	PASS	3X	PASS	X	PASS	QBS to QBS Device 3		X	PASS
	HTSL (JESD22-A103) Ta>150C			168 Hrs	0/77		QBS to QBS Device 1		QBS to QBS Device 2		X	PASS	QBS to QBS Device 1		QBS to QBS Device 2		QBS to Qual Device 3/ QBS Device 5		3X	PASS	3X	PASS	X	PASS	QBS to QBS Device 3		X	PASS
	High Temperature Storage			500 Hrs	0/77		QBS to QBS Device 1																					